

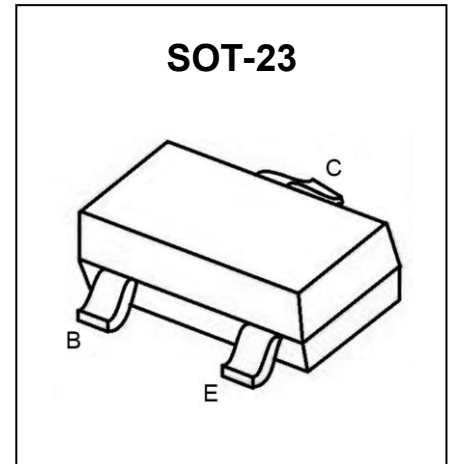


**A1015 Transistor(PNP)**

**Feature**

- High voltage and high current
- Excellent  $h_{FE}$  linearity
- Complementary to C1815

**Marking: BA**



**MAXIMUM RATINGS ( $T_a=25^{\circ}\text{C}$  unless otherwise noted)**

Parameter	Symbol	Value	Unit
Collector-Base Voltage	$V_{CB0}$	-50	V
Collector-Emitter Voltage	$V_{CE0}$	-50	V
Emitter-Base Voltage	$V_{EB0}$	-5	V
Collector Current -Continuous	$I_c$	-0.15	A
Power Dissipation	$P_d$	0.2	W
Thermal Resistance Form Junction to Ambient	$R_{\theta JA}$	625	$^{\circ}\text{C}/\text{W}$
Junction Temperature	$T_J$	150	$^{\circ}\text{C}$
Storage Temperature	$T_{STG}$	-55~ +150	$^{\circ}\text{C}$

**CLASSIFICATION OF  $h_{FE}$**

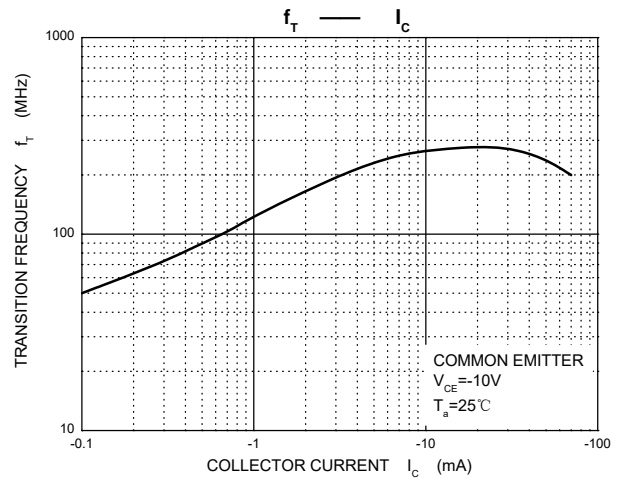
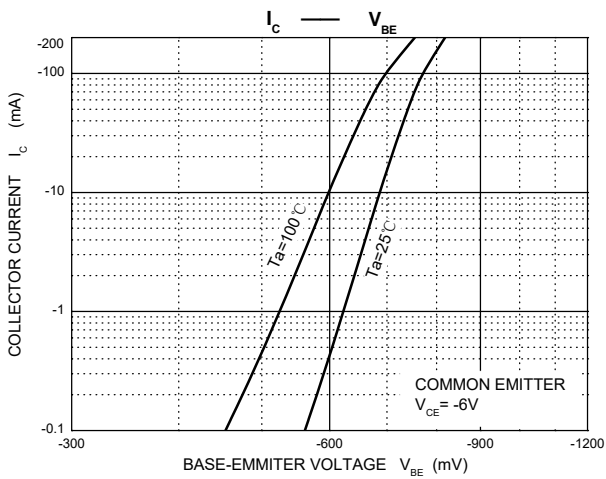
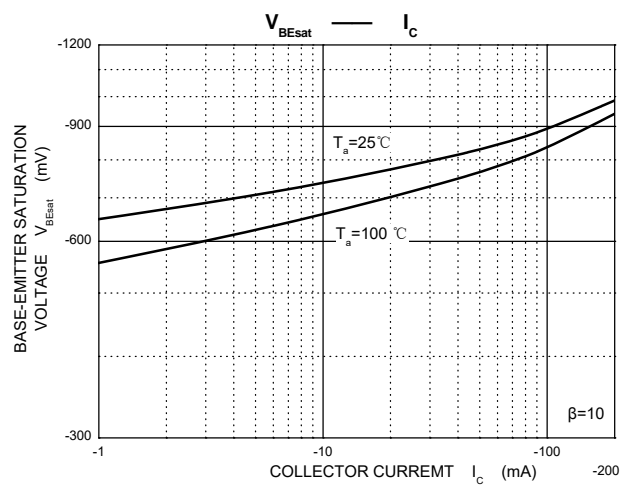
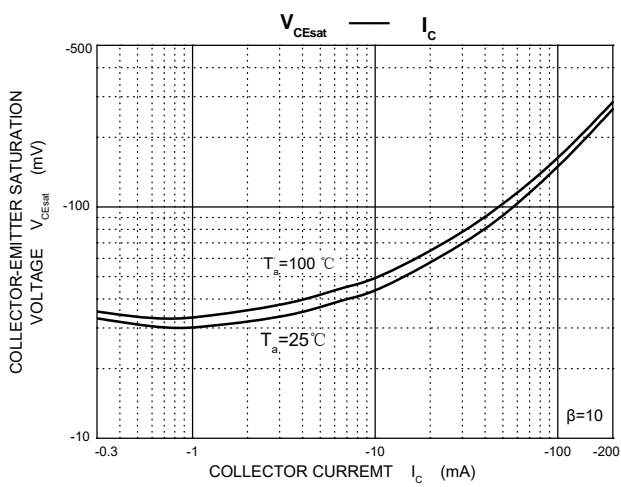
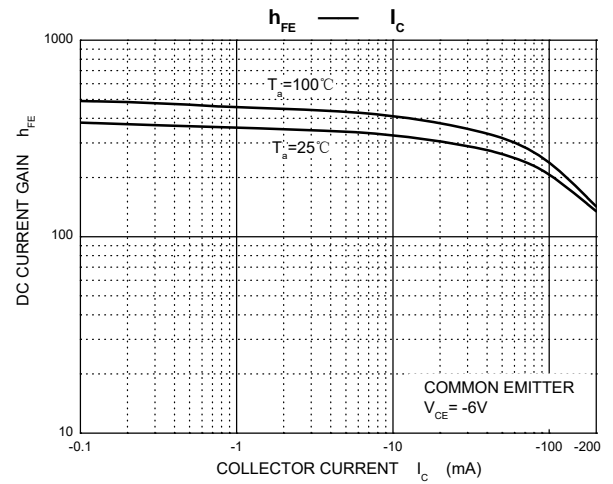
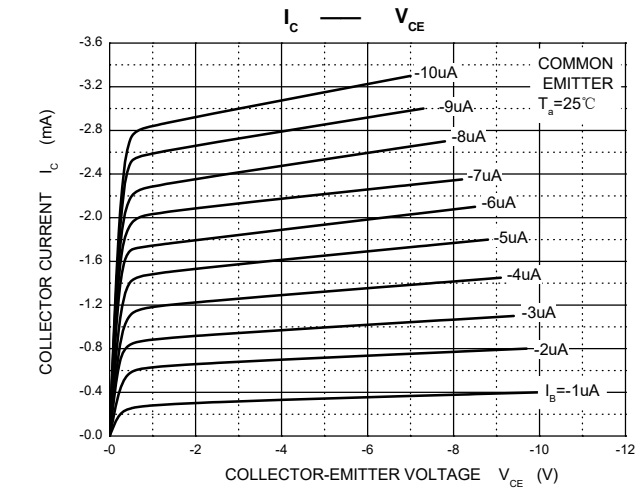
Rank	L	H
Range	120~240	200~400

**ELECTRICAL CHARACTERISTICS(T<sub>a</sub>=25°C unless otherwise noted)**

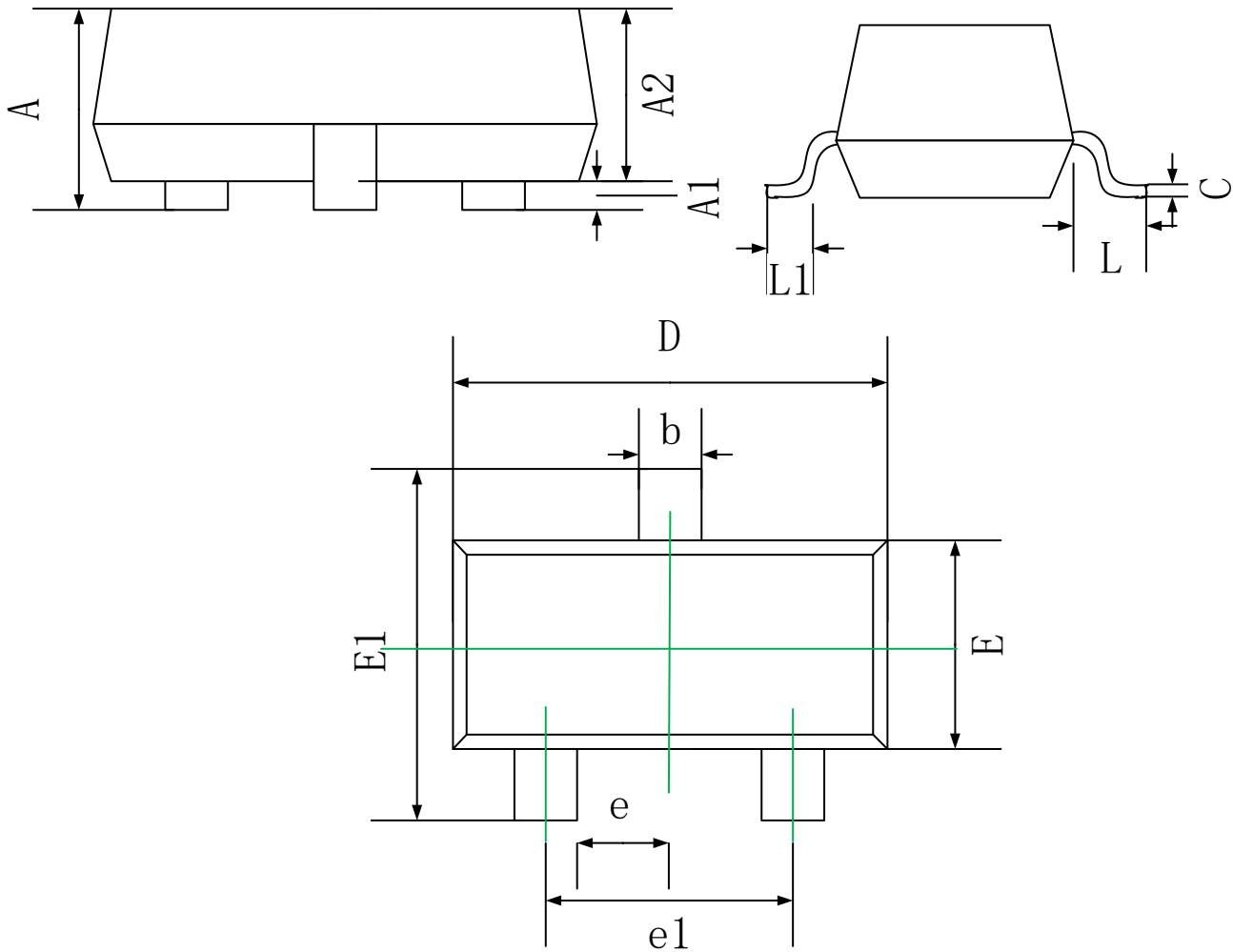
Parameter	Symbol	Test Condition	Min	Max	Unit
Collector-base breakdown voltage	V(BR) <sub>CBO</sub>	I <sub>C</sub> =-100μA, I <sub>E</sub> =0	-50		V
Collector-emitter breakdown voltage	V(BR) <sub>CEO</sub>	I <sub>C</sub> =-0.1mA, I <sub>B</sub> =0	-50		V
Emitter-base breakdown voltage	V(BR) <sub>EBO</sub>	I <sub>E</sub> =-100μA, I <sub>C</sub> =0	-5		V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =-50V, I <sub>E</sub> =0		-100	nA
Collector cut-off current	I <sub>CEX</sub>	V <sub>CE</sub> =-25V, I <sub>B</sub> =0		-100	nA
Base cut-off current	I <sub>BEX</sub>	V <sub>CE</sub> =-25V, I <sub>B</sub> =0		-100	nA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =-5V, I <sub>C</sub> =0		-100	nA
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> =-5V, I <sub>C</sub> =-1mA	130	400	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-10mA, I <sub>B</sub> =-1mA		-0.2	V
		I <sub>C</sub> =-100mA, I <sub>B</sub> =-10mA		-0.3	V
Base-emitter saturation voltage*	V <sub>BE(sat)</sub>	I <sub>C</sub> =-10mA, I <sub>B</sub> =-1mA		-0.85	V
		I <sub>C</sub> =-100mA, I <sub>B</sub> =-10mA		-0.95	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =-5V, I <sub>C</sub> =-10mA, f=30MHz	150		MHz
Delay time	t <sub>d</sub>	V <sub>CC</sub> =-3V, V <sub>BE</sub> =-0.5V,		35	ns
Rise time	t <sub>r</sub>	I <sub>C</sub> =-10mA, I <sub>B</sub> =-1mA		35	ns
Storage time	t <sub>s</sub>	V <sub>CC</sub> =-3V, V <sub>BE</sub> =-0.5V,		200	ns
Fall time	t <sub>f</sub>	I <sub>B1</sub> =I <sub>B2</sub> =-1mA		50	ns

\*Pulse Test: Pulse Width<300us, Duty Cycle<2.0%

**Typical Characteristics**



## SOT-23 Package Information



Symbol	Dimensions In Millimeters	
	Min.	Max.
A	0.900	1.150
A1	0.000	0.125
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.95 REF.	
e1	1.800	2.000
L	0.55 REF.	
L1	0.300	0.500